

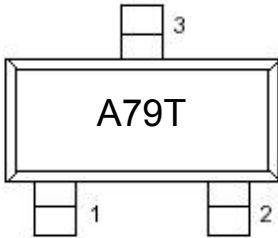
# CDL3407A-ME

## MOSFET

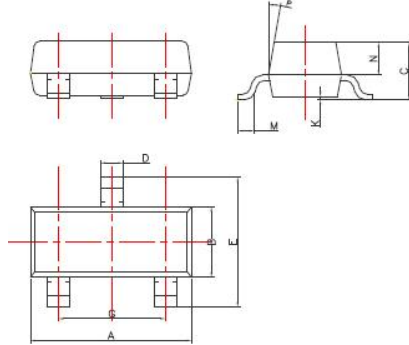
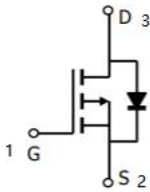
Marking: A79T

SOT-23 Dimension

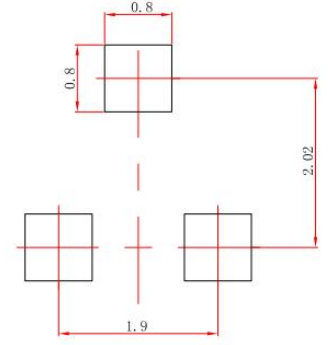
SOT-23 Suggested Layout



Top view



DIM	Millimeters
A	2.85~3.04
B	1.30±0.10
C	1.00±0.10
D	0.45±0.05
E	2.25~2.55
G	1.90±0.1
K	0.00-0.10
M	0.20 MIN
N	0.60±0.10
P	7±2°



mm(±0.05mm)

### MAXIMUM RATINGS (T<sub>a</sub>=25°C)

Characteristic	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-30	Vdc
Gate-Source Voltage	V <sub>GSS</sub>	±20	Vdc
Drain Current—Continuous	I <sub>D</sub>	-4.1	Adc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board(1) T <sub>A</sub> =25°C	PD	225	mW
Total Device Dissipation Alumina Substrate,(2) T <sub>A</sub> =25°C	P <sub>D</sub>	300	mW
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	150, -55 to +150	°C

- FR-5=1.0×0.75×0.062in, printed-circuit board.
- Alumina=0.4×0.3×0.024in, 99.5%alumina

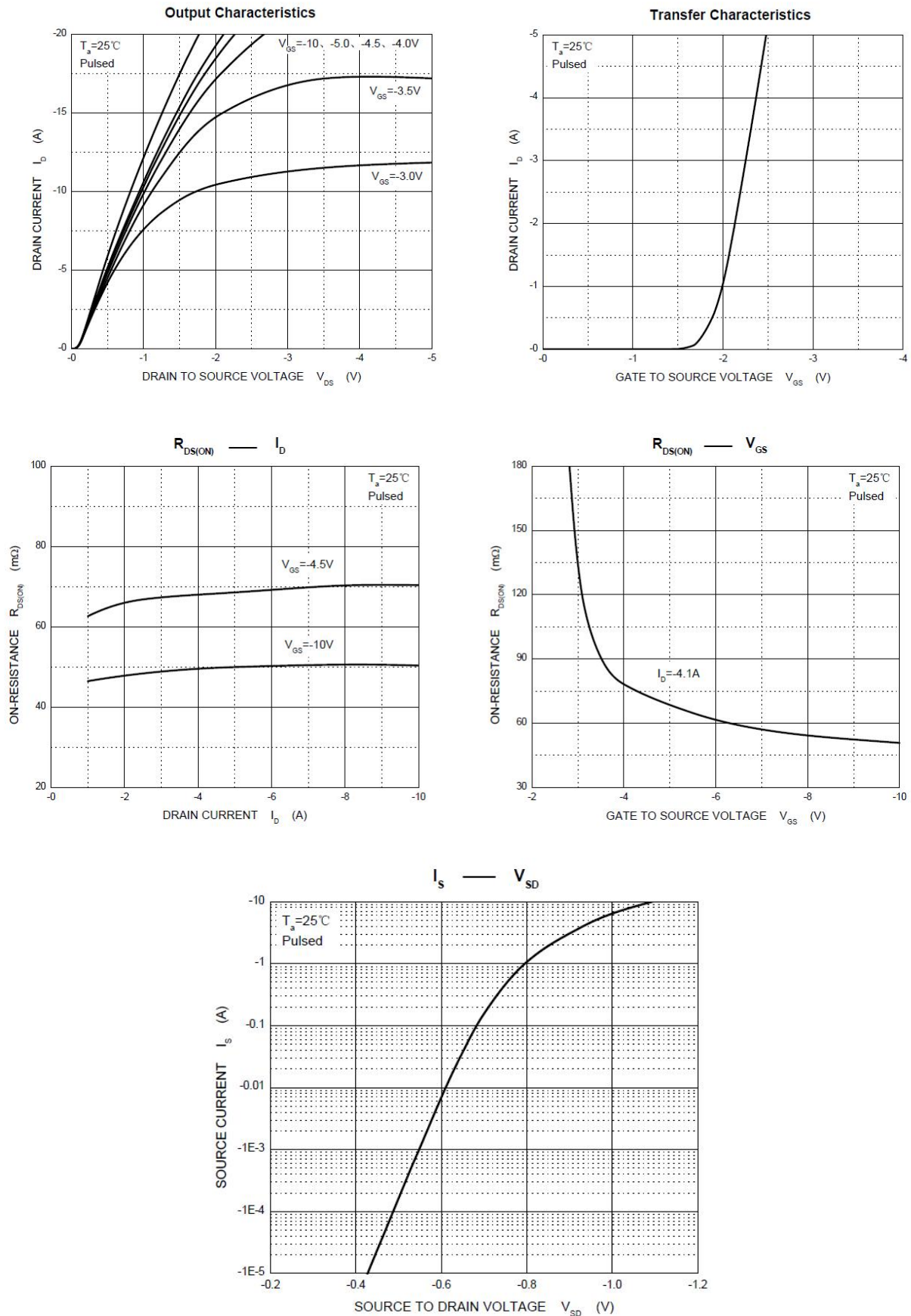
### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Type	Max	Unit
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current,Forward	I <sub>GSS</sub>	V <sub>GS</sub> =±20V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-	-3	V
Static Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.1A V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	-	48 60	65 95	mΩ
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = -5V, I <sub>D</sub> =-4A	5.5	-	-	S
Diode Forward On-Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A	-	-	-1.2	V
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-6V, I <sub>D</sub> =-1A, V <sub>GS</sub> =-4.5V, R <sub>GEN</sub> = 6Ω	-	8.5	-	ns
Turn-On Time	t <sub>r</sub>		-	4.5	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	26	-	
Turn-On Fall Time	t <sub>f</sub>		-	12.5	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-6V, V <sub>GS</sub> = 0V, f = 1.0 MHz	-	700	-	pF
Output Capacitance	C <sub>oss</sub>		-	120	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	75	-	

# CDL3407A-ME

## MOSFET

### Typical Performance Characteristics



Note: Specifications are subject to change without notice. For more detail and update, please visit our website.